

**X-Band Radar 50Ω Transistor - GaN**

<ul style="list-style-type: none"> <li>■ GaN on SiC HEMT Technology</li> <li>■ <math>P_{OUT-PK} = 50W @ 100\mu s/10\%/50V</math></li> <li>■ 9.0-10.0GHz Instantaneous Operating Frequency Range</li> <li>■ 50Ω Internally Impedance Matched Device</li> <li>■ Depletion Mode Device</li> <li>■ Negative Gate Voltage and Bias Sequencing Required</li> <li>■ Metal Based Package Sealed With Ceramic-Epoxy Lid</li> <li>■ Gold Metallization System: Chip - Wire Bond - Package</li> <li>■ Package Size Bolt Down: W=0.945"(24mm), L=0.685"(17.4mm)</li> <li>■ 100% High Power RF Tested in Broadband RF Test Fixture</li> </ul>	<p>See package options page 3</p>
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PARAMETER	SYM	MIN	TYP	MAX	UNITS	TEST CONDITIONS
<b>DC ELECTRICAL SPECIFICATIONS</b>						
Drain Leakage Current	$I_{D-OFF}$	--	--	2	mA	$V_{DS}=50V, V_{GS}=-6V, T_{F1}, S1$
Gate Threshold Voltage	$V_{GS-TH}$	-3.3	-2.3	-1.5	V	$V_{DS}=50V, I_D=10mA, T_{F1}, S1$
<b>RF ELECTRICAL SPECIFICATIONS</b>						
Input Return Loss	IRL	-18	-10	-5	dB	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Power Gain	Gp	--	10.0	--	dB	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Drain Efficiency	$N_D$	--	37	--	%	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Pulse Amplitude Droop	D	--	-0.40	--	dB	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Delta Inter-pulse Insertion Phase-Note 1	DIP	-30	--	+30	DEG	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F3, $T_{F1}, S1, N1$
Load Mismatch Stability	VSWR-S	2:1	--	--	--	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Load Mismatch Tolerance	VSWR-T	3:1	--	--	--	POUT1, V1, $I_{DQ1}$ , PW1, DF1, F1, F2, F3, $T_{F1}, S1$

DC & RF TEST CONDITIONS	SYM	MIN	NOM	MAX	UNITS	TEST CONDITIONS
Output Power 1	POUT1	--	50	--	W	--
Drain Supply Voltage 1	V1	--	50.0	--	V	--
Quiescent Drain Current 1	$I_{DQ1}$	--	10	--	mA	--
Pulse Width 1	PW1	--	100	--	us	--
Duty Factor 1	DF1	--	10	--	%	--
Frequency 1	F1	--	9.0	--	GHz	--
Frequency 2	F2	--	9.5	--	GHz	--
Frequency 3	F3	--	10.0	--	GHz	--
Flange Temperature 1	$T_{F1}$	20	25	30	°C	--

PARAMETER	SYM	MIN	MAX	UNITS	SCREEN	CONDITIONS
<b>MAXIMUM RATINGS</b>						
Drain-Source Voltage	$V_{DS}$	--	55	V	BD	$T_F = 25^\circ\text{C}$
Gate-Source Voltage	$V_{GS}$	-10	0	V	BD	$T_F = 25^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55	+150	$^\circ\text{C}$	BD	--
Operating Junction Temperature	$T_J$	-55	+200	$^\circ\text{C}$	BD	--
<b>PROCESS SPECIFICATIONS</b>						
DC Wafer Probe	--	--	--	--	100%	Per Integra Spec
Wafer DC, RF Qualification	--	--	--	--	Q1	Per Integra Spec
Wire Bond Strength	--	--	--	--	LM	Per Integra Spec
Pre-cap Visual Inspection	--	--	--	--	100%	Per Integra Spec
Gross Leak Test – MIL-STD-750D	--	--	--	--	100%	Method 1071.6 C
<b>THERMAL RESISTANCE</b>						
Peak Thermal Resistance Per Rated RF Specification	$R_{TH(JC)}$	--	TBD	$^\circ\text{C/W}$	BD	$T_F = 25^\circ\text{C}$
<b>SCREENING LEVELS</b>						
Parameter Qualified By Design	BD	--	--	--	--	--
Parameter Qualified By 3 Pieces (min) Per Wafer	Q1	--	--	--	--	--
Parameter Qualified By Assembly Line Monitor	LM	--	--	--	--	--
Screening Level 1	S1	--	--	--	100%	--
<b>NOTES</b>						
	N1	All devices are marked with delta insertion phase dash numbers, as INTEGRA-XX, with "XX" from -1 thru -12 indicating 5° variations between -30° to +30° from reference.				

RF TEST FIXTURE – 50Ω BROADBAND
▶ Broadband RF Test Fixture. Provides 50Ω Impedance To the Device Across the Rated Operating Frequency Range.
▶ Electronic CAD Drawing File Available Upon Request. Includes Circuit Dimensions and Parts List.
▶ Reference Design PCB: TBD

DC BIAS SEQUENCING	
<b>Turn ON GaN Device</b> 1. RF Power OFF 2. Set VGS = -5V (Negative Voltage to pinch off) 3. Measure VDS impedance, should be pinched off. 4. Turn ON VDD voltage. 5. Slowly increase VGS until bias current IDQ is set. 6. Turn ON RF Power	<b>Turn OFF GaN Device</b> 1. Turn OFF RF Power 2. Turn OFF VDD voltage 3. After VDD is discharged, set VGS = -5V 4. Turn OFF VGS voltage.



DEFINITIONS	
<b>DATA SHEET STATUS</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>MAXIMUM RATINGS</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

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